Armin Dadgar

List of Publications by Year
in descending order

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250	7,565	50276	64796
papers	citations	46 h-index	79 g-index

259	259	259	5459
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Metalorganic Chemical Vapor Phase Epitaxy of Crack-Free GaN on Si (111) Exceeding 1 Âµm in Thickness. Japanese Journal of Applied Physics, 2000, 39, L1183-L1185.	1.5	310
2	GaN-based optoelectronics on silicon substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 77-84.	3.5	268
3	Template-Assisted Large-Scale Ordered Arrays of ZnO Pillars for Optical and Piezoelectric Applications. Small, 2006, 2, 561-568.	10.0	209
4	Thick, crack-free blue light-emitting diodes on Si(111) using low-temperature AlN interlayers andin situSixNy masking. Applied Physics Letters, 2002, 80, 3670-3672.	3.3	183
5	Gallium nitride vertical power devices on foreign substrates: a review and outlook. Journal Physics D: Applied Physics, 2018, 51, 273001.	2.8	173
6	GaN-Based Devices on Si. Physica Status Solidi A, 2002, 194, 361-375.	1.7	164
7	High Si and Ge n-type doping of GaN doping - Limits and impact on stress. Applied Physics Letters, 2012, 100, .	3.3	160
8	Arrays of vertically aligned and hexagonally arranged ZnO nanowires: a new template-directed approach. Nanotechnology, 2005, 16, 913-917.	2.6	147
9	High-sheet-chargeâ€“carrier-density AlInNâˆ•GaN field-effect transistors on Si(111). Applied Physics Letters, 2004, 85, 5400-5402.	3.3	133
10	Band gap renormalization and Burstein-Moss effect in silicon- and germanium-doped wurtzite GaN up to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msup><mml:mrow><mml:mn>10</mml:mn></mml:mrow><mml:mn>20</ mathvariant="normal">cm</mml:mi><mml:msup><mml:mrow /><mml:mrow><mml:mo>â^’</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:msup></mml:math>. Physical Review B, 2014, 90, .	3.2	133
11	MOVPE growth of GaN on Si(111) substrates. Journal of Crystal Growth, 2003, 248, 556-562.	1.5	125
12	GaN-based epitaxy on silicon: stress measurements. Physica Status Solidi A, 2003, 200, 26-35.	1.7	125
13	Epitaxy of GaN on siliconâ€”impact of symmetry and surface reconstruction. New Journal of Physics, 2007, 9, 389-389.	2.9	124
14	Metal-organic vapor phase epitaxy and properties of AlInN in the whole compositional range. Applied Physics Letters, 2007, 90, 022105.	3.3	119
15	The origin of stress reduction by low-temperature AlN interlayers. Applied Physics Letters, 2002, 81, 2722-2724.	3.3	117
16	Efficient stress relief in GaN heteroepitaxy on Si(111) using low-temperature AlN interlayers. Journal of Crystal Growth, 2003, 248, 563-567.	1.5	117
17	Growth of blue GaN LED structures on 150-mm Si(111). Journal of Crystal Growth, 2006, 297, 279-282.	1.5	117
18	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1583-1606.	0.8	116

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19	Atomic arrangement at the AlN/Si (111) interface. Applied Physics Letters, 2003, 83, 860-862.	3.3	114
20	Piezoelectric GaN sensor structures. IEEE Electron Device Letters, 2006, 27, 309-312.	3.9	113
21	Recording of cell action potentials with AlGaNâˆ•GaN field-effect transistors. Applied Physics Letters, 2005, 86, 033901.	3.3	112
22	Dislocation annihilation by silicon delta-doping in GaN epitaxy on Si. Applied Physics Letters, 2002, 81, 4712-4714.	3.3	109
23	Well-ordered ZnO nanowire arrays on GaN substrate fabricated via nanosphere lithography. Journal of Crystal Growth, 2006, 287, 34-38.	1.5	108
24	Bright blue electroluminescence from an InGaN/GaN multiquantum-well diode on Si(111): Impact of an AlGaN/GaN multilayer. Applied Physics Letters, 2001, 78, 2211-2213.	3.3	106
25	Reduction of stress at the initial stages of GaN growth on Si(111). Applied Physics Letters, 2003, 82, 28-30.	3.3	102
26	Vapour-transport-deposition growth of ZnO nanostructures: switch betweenc-axial wires anda-axial belts by indium doping. Nanotechnology, 2006, 17, S231-S239.	2.6	97
27	Laser-Interference Lithography Tailored for Highly Symmetrically Arranged ZnO Nanowire Arrays. Small, 2007, 3, 76-80.	10.0	95
28	Fabrication, Self-Assembly, and Properties of Ultrathin AlN/GaN Porous Crystalline Nanomembranes: Tubes, Spirals, and Curved Sheets. ACS Nano, 2009, 3, 1663-1668.	14.6	91
29	Local p-type conductivity in zinc oxide dual-doped with nitrogen and arsenic. Applied Physics Letters, 2005, 87, 262105.	3.3	90
30	Two charge states of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">C</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:msub></mml:math> acceptor in GaN: Evidence from photoluminescence. Physical Review B, 2018, 98, .	3.2	84
31	MOVPE growth of GaN on Si â€“ Substrates and strain. Thin Solid Films, 2007, 515, 4356-4361.	1.8	81
32	Transient Thermal Characterization of AlGaN/GaN HEMTs Grown on Silicon. IEEE Transactions on Electron Devices, 2005, 52, 1698-1705.	3.0	78
33	Sixteen years GaN on Si. Physica Status Solidi (B): Basic Research, 2015, 252, 1063-1068.	1.5	76
34	Crack-Free, Highly Conducting GaN Layers on Si Substrates by Ge Doping. Applied Physics Express, 2011, 4, 011001.	2.4	73
35	Patterned growth of aligned ZnO nanowire arrays on sapphire and GaN layers. Superlattices and Microstructures, 2004, 36, 95-105.	3.1	70
36	High-Performance 500 V Quasi- and Fully-Vertical GaN-on-Si pn Diodes. IEEE Electron Device Letters, 2017, 38, 248-251.	3.9	70

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37	Fabry-Perot effects in InGaNâˆ•GaN heterostructures on Si-substrate. Journal of Applied Physics, 2007, 101, 033113.	2.5	69
38	MOVPE growth of high-quality AlN. Journal of Crystal Growth, 2006, 297, 306-310.	1.5	68
39	Dielectric function and optical properties of Al-rich AlInN alloys pseudomorphically grown on GaN. Journal Physics D: Applied Physics, 2010, 43, 365102.	2.8	66
40	P-Channel InGaN-HFET Structure Based on Polarization Doping. IEEE Electron Device Letters, 2004, 25, 450-452.	3.9	62
41	Improving GaNâ€onâ€silicon properties for GaN device epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1503-1508.	0.8	59
42	All metalorganic chemical vapor phase epitaxy of p/n-GaN tunnel junction for blue light emitting diode applications. Applied Physics Letters, 2017, 110, .	3.3	59
43	Thermal stability of metal organic vapor phase epitaxy grown AlInN. Applied Physics Letters, 2007, 90, 221906.	3.3	53
44	Self-assembly of ZnO nanowires and the spatial resolved characterization of their luminescence. Nanotechnology, 2004, 15, 1401-1404.	2.6	52
45	A two-step metal organic vapor phase epitaxy growth method for high-quality ZnO on GaN/Al2O3 (0001). Journal of Crystal Growth, 2004, 267, 140-144.	1.5	52
46	Crack-Free InGaN/GaN Light Emitters on Si(111). Physica Status Solidi A, 2001, 188, 155-158.	1.7	48
47	Decoration effects as origin of dislocation-related charges in gallium nitride layers investigated by scanning surface potential microscopy. Applied Physics Letters, 2003, 82, 2263-2265.	3.3	48
48	Metalorganic chemical vapor phase deposition of ZnO with different O-precursors. Journal of Crystal Growth, 2003, 248, 14-19.	1.5	46
49	Influence of buffer layers on metalorganic vapor phase epitaxy grown GaN on Si(001). Applied Physics Letters, 2004, 84, 4747-4749.	3.3	46
50	Influence of exciton-phonon coupling and strain on the anisotropic optical response of wurtzite AlN around the band edge. Physical Review B, 2011, 83, .	3.2	46
51	UNSTRAINED InAlN/GaN HEMT STRUCTURE. International Journal of High Speed Electronics and Systems, 2004, 14, 785-790.	0.7	42
52	Metalorganic vapor phase epitaxy grown InGaNâˆ•GaN light-emitting diodes on Si(001) substrate. Applied Physics Letters, 2006, 88, 121114.	3.3	42
53	Bright, Crack-Free InGaN/GaN Light Emitters on Si(111). Physica Status Solidi A, 2002, 192, 308-313.	1.7	41
54	In situ measurements of strains and stresses in GaN heteroepitaxy and its impact on growth temperature. Journal of Crystal Growth, 2004, 272, 72-75.	1.5	41

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55	In situ monitoring of the stress evolution in growing group-III-nitride layers. Journal of Crystal Growth, 2005, 275, 209-216.	1.5	40
56	Germanium - the superior dopant in n-type GaN. Physica Status Solidi - Rapid Research Letters, 2015, 9, 716-721.	2.4	40
57	Ostwald ripening and flattening of epitaxial ZnO layers during in situ annealing in metalorganic vapor phase epitaxy. Applied Physics Letters, 2004, 85, 1496-1498.	3.3	39
58	Reduction of on-resistance and current crowding in quasi-vertical GaN power diodes. Applied Physics Letters, 2017, 111, .	3.3	39
59	Evolution of stress in GaN heteroepitaxy on AlNâˆ•Si(111): From hydrostatic compressive to biaxial tensile. Applied Physics Letters, 2004, 85, 3441-3443.	3.3	38
60	Homoepitaxial growth of ZnO by metalorganic vapor phase epitaxy in two-dimensional growth mode. Journal of Crystal Growth, 2007, 308, 170-175.	1.5	37
61	High-current AlInN/GaN field effect transistors. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 832-836.	1.8	36
62	Two-dimensional electron gas based actuation of piezoelectric AlGaN/GaN microelectromechanical resonators. Applied Physics Letters, 2008, 93, .	3.3	36
63	Role of low-temperature AlGaN interlayers in thick GaN on silicon by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	2.5	36
64	InGaN/GaN light-emitting diodes on Si(1â€‰1â€‰0) substrates grown by metalâ€“organic vapour phase epitaxy. Journal Physics D: Applied Physics, 2009, 42, 055107.	2.8	35
65	In Ga N âˆ• Ga N light emitting diodes on nanoscale silicon on insulator. Applied Physics Letters, 2007, 91, .	3.3	34
66	Optical and structural microanalysis of GaN grown on SiN submonolayers. Journal of Applied Physics, 2006, 99, 123518.	2.5	33
67	Growth of single-domain GaN layers on Si(001) by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2006, 289, 485-488.	1.5	33
68	Anisotropy of effective electron masses in highly doped nonpolar GaN. Applied Physics Letters, 2013, 103, .	3.3	33
69	Properties of Câ€doped GaN. Physica Status Solidi (B): Basic Research, 2017, 254, 1600708.	1.5	33
70	Ruthenium: A superior compensator of InP. Applied Physics Letters, 1998, 73, 3878-3880.	3.3	32
71	Complex excitonic recombination kinetics in ZnO: Capture, relaxation, and recombination from steady state. Applied Physics Letters, 2007, 90, 041917.	3.3	31
72	Methodology for the investigation of threading dislocations as a source of vertical leakage in AlGaN/GaN-HEMT heterostructures for power devices. Journal of Applied Physics, 2019, 125, .	2.5	30

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73	Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. Applied Physics Letters, 2015, 106, .	3.3	29
74	Analysis of point defects in AlN epilayers by cathodoluminescence spectroscopy. Applied Physics Letters, 2009, 95, .	3.3	28
75	ZnO MOVPE growth: From local impurity incorporation towards p-type doping. Superlattices and Microstructures, 2005, 38, 245-255.	3.1	27
76	Metal organic vapor phase epitaxy growth of single crystalline GaN on planar Si(211) substrates. Applied Physics Letters, 2009, 95, .	3.3	27
77	Valence-band splitting and optical anisotropy of AlN. Physica Status Solidi (B): Basic Research, 2010, 247, 1679-1682.	1.5	26
78	On reduction of current leakage in GaN by carbon-doping. Applied Physics Letters, 2016, 109, .	3.3	25
79	GaN micromachined FBAR structures for microwave applications. Superlattices and Microstructures, 2006, 40, 426-431.	3.1	24
80	Metal Organic Vapor Phase Epitaxy of ZnO on GaN/Si(111) Using Tertiary-Butanol as O-Precursor. Japanese Journal of Applied Physics, 2003, 42, 7474-7477.	1.5	23
81	Wafer curvature in the nonlinear deformation range. Physica Status Solidi A, 2004, 201, R75-R78.	1.7	23
82	Modulation spectroscopy of AlGaN/GaN heterostructures: The influence of electron-hole interaction. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 447-458.	1.8	23
83	Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. Journal of Applied Physics, 2017, 122, .	2.5	23
84	Influence of excitons and electric fields on the dielectric function of GaN: Theory and experiment. Physical Review B, 2006, 74, .	3.2	22
85	Epitaxy of GaN LEDs on large substrates: Si or sapphire?. , 2006, , .		22
86	Semipolar single component GaN on planar high index Si(11h) substrates. Applied Physics Letters, 2010, 97, .	3.3	22
87	Eliminating stacking faults in semi-polar GaN by AlN interlayers. Applied Physics Letters, 2011, 99, 021905.	3.3	22
88	Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. Journal of Crystal Growth, 2015, 414, 105-109.	1.5	22
89	Atomic Arrangement at the AlN/Si(110) Interface. Applied Physics Express, 0, 1, 061104.	2.4	21
90	Strain evaluation in AlInN/GaN Bragg mirrors by in situ curvature measurements and ex situ x-ray grazing incidence and transmission scattering. Applied Physics Letters, 2010, 97, .	3.3	21

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91	Low-temperature/high-temperature AlN superlattice buffer layers for high-quality AlxGa1â^'xN on Si (111). Journal of Crystal Growth, 2009, 311, 3742-3748.	1.5	20
92	InAlN/GaN/Si heterostructures and field-effect transistors with lattice matched and tensely or compressively strained InAlN. Applied Physics Letters, 2010, 97, 173505.	3.3	19
93	Reliable GaN-Based THz Gunn Diodes With Side-Contact and Field-Plate Technologies. IEEE Access, 2020, 8, 84116-84122.	4.2	19
94	Gallium-nitride-based devices on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1940-1949.	0.8	18
95	In-situ growth monitoring of AlInN/AlGaN distributed Bragg reflectors for the UV-spectral range. Journal of Crystal Growth, 2013, 370, 87-91.	1.5	18
96	Ge as a surfactant in metal-organic vapor phase epitaxy growth of a-plane GaN exceeding carrier concentrations of 1020Âcmâ^'3. Applied Physics Letters, 2013, 103, .	3.3	18
97	Capacitance transient study of the deep Fe acceptor in indium phosphide. Physical Review B, 1997, 56, 10241-10248.	3.2	17
98	Growth of Ru doped semi-insulating InP by low pressure metalorganic chemical vapor deposition. Journal of Crystal Growth, 1998, 195, 69-73.	1.5	17
99	Electrical microcharacterization of dislocation-related charges in GaN-based single layers by scanning probe microscopy techniques. Journal of Crystal Growth, 2003, 248, 542-547.	1.5	17
100	Time-delayed indium incorporation in ultrathin (InxGa1â^'xN/GaN) multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2003, 82, 4558-4560.	3.3	17
101	A low-temperature evaporation route for ZnO nanoneedles and nanosaws. Applied Physics A: Materials Science and Processing, 2005, 80, 457-460.	2.3	17
102	Metalorganic vapor-phase epitaxy of GaN layers on Si substrates with Si(110) and other high-index surfaces. Journal of Crystal Growth, 2010, 312, 180-184.	1.5	17
103	Heavy Si doping: The key in heteroepitaxial growth of aâ€plane GaN without basal plane stacking faults?. Physica Status Solidi (B): Basic Research, 2011, 248, 578-582.	1.5	17
104	Phonons and free-carrier properties of binary, ternary, and quaternary group-III nitride layers measured by Infrared Spectroscopic Ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1750-1769.	0.8	16
105	Heteroepitaxy and nitrogen doping of high-quality ZnO. Journal of Crystal Growth, 2004, 272, 800-804.	1.5	16
106	GaN heteroepitaxy on Si(001). Journal of Crystal Growth, 2004, 272, 496-499.	1.5	16
107	Electroreflectance spectroscopy of Ptâ^•AlGaNâ^•GaN heterostructures exposed to gaseous hydrogen. Applied Physics Letters, 2006, 88, 024101.	3.3	16
108	Temperature rise in InGaN/GaN vertical light emitting diode on copper transferred from silicon probed by Raman scattering. Journal of Applied Physics, 2010, 108, .	2.5	16

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109	Growth and stacking fault reduction in semiâ€polar GaN films on planar Si(112) and Si(113). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 507-510.	0.8	16
110	Breakdown of Far-Field Raman Selection Rules by Lightâ€“Plasmon Coupling Demonstrated by Tip-Enhanced Raman Scattering. Journal of Physical Chemistry Letters, 2017, 8, 5462-5471.	4.6	16
111	Bright blue to orange photoluminescence emission from high-quality InGaN/GaN multiple-quantum-wells on Si(111) substrates. Applied Physics Letters, 2002, 81, 1591-1593.	3.3	15
112	Growth of ZnO Layers by Metal Organic Chemical Vapor Phase Epitaxy. Physica Status Solidi A, 2002, 192, 189-194.	1.7	15
113	Thin-film InGaNâ•GaN Vertical Light Emitting Diodes Using GaN on Silicon-On-Insulator Substrates. Electrochemical and Solid-State Letters, 2011, 14, H460.	2.2	15
114	MOVPE growth of semi-polar GaN light-emitting diode structures on planar Si(112) and Si(113) substrates. Journal of Crystal Growth, 2013, 370, 288-292.	1.5	15
115	Deep-level transient-spectroscopy study of rhodium in indium phosphide. Physical Review B, 1996, 53, 7190-7196.	3.2	14
116	Surface stability of InGaN-channel based HFETs. Electronics Letters, 2003, 39, 1614.	1.0	14
117	Anisotropic bow and plastic deformation of GaN on silicon. Journal of Crystal Growth, 2013, 370, 278-281.	1.5	14
118	Direct evidence for selective impurity incorporation at the crystal domain boundaries in epitaxial ZnO layers. Applied Physics Letters, 2004, 85, 1976-1978.	3.3	13
119	Depth-resolving structural analysis of GaN layers by skew angle x-ray diffraction. Applied Physics Letters, 2004, 84, 3537-3539.	3.3	13
120	Simultaneous measurement of wafer curvature and true temperature during metalorganic growth of group-III nitrides on silicon and sapphire. Physica Status Solidi (B): Basic Research, 2005, 242, 2570-2574.	1.5	13
121	Green to blue polarization compensated c-axis oriented multi-quantum wells by AlGaInN barrier layers. Applied Physics Letters, 2013, 102, .	3.3	13
122	Thermal stability of the midgap acceptor rhodium in indium phosphide. Applied Physics Letters, 1995, 67, 479-481.	3.3	12
123	Temperature dependence of the built-in electric field strength of AlGaN/GaN heterostructures on Si(111) substrate. Superlattices and Microstructures, 2004, 36, 693-700.	3.1	12
124	Crystallographic and electric properties of MOVPE-grown AlGaN/GaN-based FETs on Si(001) substrates. Journal of Crystal Growth, 2007, 299, 399-403.	1.5	12
125	Microâ€structural anisotropy of aâ€plane GaN analyzed by high resolution Xâ€ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S498.	0.8	12
126	Cathodoluminescence of epitaxial GaN and ZnO thin films for scintillator applications. Journal of Crystal Growth, 2009, 311, 3984-3988.	1.5	12

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127	Microstructure of gallium nitride films grown on silicon (110). Applied Physics Letters, 2010, 96, 231908.	3.3	12
128	Luminescence from two-dimensional electron gases in InAlN/GaN heterostructures with different In content. Applied Physics Letters, 2012, 100, .	3.3	12
129	Growth and characterization of stacking fault reduced GaN $(1,0,ar{1},3)$ on sapphire. Journal Physics D: Applied Physics, 2013, 46, 125308.	2.8	12
130	Local p-type conductivity in n-GaN and n-ZnO layers due to inhomogeneous dopant incorporation. Physica B: Condensed Matter, 2006, 376-377, 703-706.	2.7	11
131	AlInN/GaN based multi quantum well structures â€“ growth and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S451.	0.8	11
132	Growth of AlInN/AlGaN distributed Bragg reflectors for high quality microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1253-1258.	0.8	11
133	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.	1.5	11
134	Radiation-induced alloy rearrangement in InxGa1â^'xN. Applied Physics Letters, 2017, 110, .	3.3	11
135	Highâ€resolution xâ€ray analysis of compressively strained 1.55 Î¼m GaInAs/AlGaInAs multiquantum well structures near the critical thickness. Applied Physics Letters, 1995, 67, 3325-3327.	3.3	10
136	MOVPE Growth and Characterization of AlInN FET Structures on Si(111). Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	10
137	Influence of anisotropic strain on excitonic transitions in a-plane GaN films. Microelectronics Journal, 2009, 40, 322-324.	2.0	10
138	Valence band tomography of wurtzite GaN by spectroscopic ellipsometry. Applied Physics Express, 2018, 11, 101001.	2.4	10
139	Metalorganic vapor phase epitaxy of ZnO: towards p-type conductivity. , 2007, 6474, 32.		9
140	Electrical investigations of AlGaN/AlN structures for LEDs on Si(111). Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1597-1599.	1.8	9
141	Flexible Modulation of Electronic Band Structures of Wide Band Gap GaN Semiconductors Using Bioinspired, Nonbiological Helical Peptides. Advanced Functional Materials, 2018, 28, 1704034.	14.9	9
142	Strain profiling of AlInN/GaN distributed Bragg reflectors using in situ curvature measurements and ex situ X-ray diffraction. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2010, 528, 58-64.	5.6	8
143	Growth of III/Vs on Silicon. , 2015, , 1249-1300.		8
144	Novel ways to grow thermally stable semi-insulating InP-based layers. Journal of Crystal Growth, 1994, 145, 455-461.	1.5	7

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145	Characterization of defects in undoped non c-plane and high resistance GaN layers dominated by stacking faults. Physica B: Condensed Matter, 2009, 404, 4922-4924.	2.7	7
146	4d- and 5d-transition metal acceptor doping of InP. Journal of Crystal Growth, 1997, 170, 173-176.	1.5	6
147	Characteristics of Alpha-Radiation-Induced Deep Level Defects in p-Type InP Grown by Metal-Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 4595-4602.	1.5	6
148	Unstrained InAlN/GaN HEMT structure. , 0, , .		6
149	Correlation between macroscopic transport parameters and microscopic electrical properties in GaN. Journal of Applied Physics, 2005, 97, 043710.	2.5	6
150	Monitoring glycolytic oscillations using AlGaN/GaN high electron mobility transistors (HEMTs). Sensors and Actuators B: Chemical, 2010, 149, 310-313.	7.8	6
151	Light extraction from GaNâ€based LED structures on siliconâ€onâ€insulator substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 88-91.	0.8	6
152	Luminescence Properties of Photonic Crystal InGaN/GaN Light Emitting Layers on Silicon-on-Insulator. Electrochemical and Solid-State Letters, 2010, 13, H343.	2.2	6
153	Direct microscopic correlation of crystal orientation and luminescence in spontaneously formed nonpolar and semipolar GaN growth domains. Applied Physics Letters, 2010, 96, .	3.3	6
154	Al_xGa_{1â^'x}N/GaN heterostructures on a thin silicon-on-insulator substrate for metalâ€“semiconductorâ€“metal photodetectors. Journal Physics D: Applied Physics, 2011, 44, 365102.	2.8	6
155	Impact of AlN seeding layer growth rate in MOVPE growth of semiâ€polar gallium nitride structures on high index silicon. Physica Status Solidi (B): Basic Research, 2011, 248, 594-599.	1.5	6
156	Characterization of AlGaInN layers using Xâ€ray diffraction and fluorescence. Physica Status Solidi (B): Basic Research, 2011, 248, 622-626.	1.5	6
157	Wafer curvature, temperature inhomogeneity, plastic deformation and their impact on the properties of GaN on silicon power and optoâ€electronic structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 397-400.	0.8	6
158	Characterization of AlInN/AlN/GaN FET structures using x-ray diffraction, x-ray reflectometry and grazing incidence x-ray fluorescence analysis. Journal Physics D: Applied Physics, 2014, 47, 355106.	2.8	6
159	Polarization engineering of câ€plane InGaN quantum wells by pulsedâ€flow growth of AlInGaN barriers. Physica Status Solidi (B): Basic Research, 2016, 253, 118-125.	1.5	6
160	Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. Applied Physics Letters, 2017, 110, .	3.3	6
161	Electronic excitations stabilized by a degenerate electron gas in semiconductors. Communications Physics, 2018, 1, .	5.3	6
162	Demonstration of lateral epitaxial growth of AlN on Si (1 1 1) at low temperatures by pulsed reactive sputter epitaxy. Journal of Crystal Growth, 2021, 571, 126250.	1.5	6

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163	Deep levels in hafnium- and zirconium-doped indium phosphide. Physical Review B, 1995, 51, 14142-14146.	3.2	5
164	Characteristics of deep levels associated with rhodium impurity in n-type GaAs. Journal of Applied Physics, 2003, 94, 3115-3120.	2.5	5
165	MOVPE growth of blue In_xGa_{1â€“x}N/GaN LEDs on 150 mm Si(001). Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2238-2240.	0.8	5
166	GaN-based microdisk light emitting diodes on (111)-oriented nanosilicon-on-insulator templates. Journal of Applied Physics, 2008, 104, 053106.	2.5	5
167	Stranskiâ€“Krastanov transition and self-organized structures in low-strained AlInN/GaN multilayer structures. Semiconductor Science and Technology, 2011, 26, 014041.	2.0	5
168	Unintentional indium incorporation into barriers of InGaN/GaN multiple quantum wells studied by photoreflectance and photoluminescence excitation spectroscopy. Journal of Applied Physics, 2016, 120, .	2.5	5
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